



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = 25°C
	$0.55\Omega @ V_{GS} = 4.5V$	0.75A
20V	0.75Ω @ V _{GS} = 2.5V	0.63A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected up to 1.5kV
- Lead-Free Finish; RoHS compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: Collector Dot
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)

ESD PROTECTED TO 1.5kV

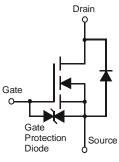


X1-DFN1006-3

Bottom View



Top View Package Pin Configuration



Equivalent Circuit

Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2400UFB-7	X1-DFN1006-3	3,000/Tape & Reel
DMN2400UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

Notes: 1. E

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

For packaging details, go to our website at http://www.diodes.com.

Marking Information



NB = Product Type Marking Code Dot Denotes Drain Side



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 4) $V_{GS} = 4.5V$	Steady State	T _A = 25°C T _A = 85°C	ID	0.75 0.55	A
Continuous Drain Current (Note 4) $V_{GS} = 2.5V$	Steady State	T _A = 25°C T _A = 85°C	ID	0.63 0.45	A
Pulsed Drain Current (Note 5)			I _{DM}	3	А

Thermal Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	PD	0.47	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	258	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current TJ = 25°C	IDSS	-	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	
Gate-Source Leakage	I _{GSS}	-	-	±50	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)	-						
Gate Threshold Voltage	V _{GS(th)}	0.5	-	0.9	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
		-	-	0.55	Ω	$V_{GS} = 4.5V, I_D = 600mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	-	0.75		$V_{GS} = 2.5V, I_D = 500mA$	
		-	-	0.9		V _{GS} = 1.8V, I _D = 350mA	
Forward Transfer Admittance	Y _{fs}	-	1.0	-	S	$V_{DS} = 10V, I_{D} = 400mA$	
Diode Forward Voltage (Note 6)	V _{SD}		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	36.0	-	pF		
Output Capacitance	Coss	-	5.7	-	pF	[−] V _{DS} = 16V, V _{GS} = 0V, −f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	4.2	-	pF	1 = 1.000112	
Total Gate Charge	Qg	-	0.5	-	nC		
Gate-Source Charge	Q _{gs}	-	0.07	-	nC	$-V_{GS} = 4.5V, V_{DS} = 10V,$ $-I_{D} = 250mA$	
Gate-Drain Charge	Q _{gd}	-	0.1	-	nC		
Turn-On Delay Time	t _{D(on)}	-	4.11	-	ns		
Turn-On Rise Time	tr	-	3.82	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	14.8	-	ns	$R_{L} = 47\Omega, R_{G} = 10\Omega,$ $R_{D} = 200 \text{mA}$	
Turn-Off Fall Time	t _f	-	9.6	-	ns		

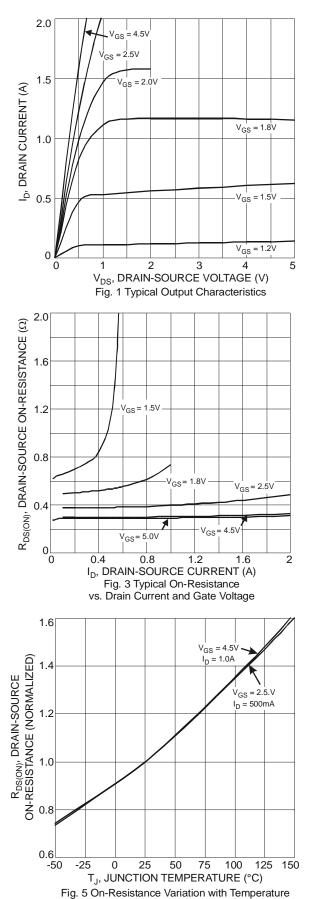
4. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

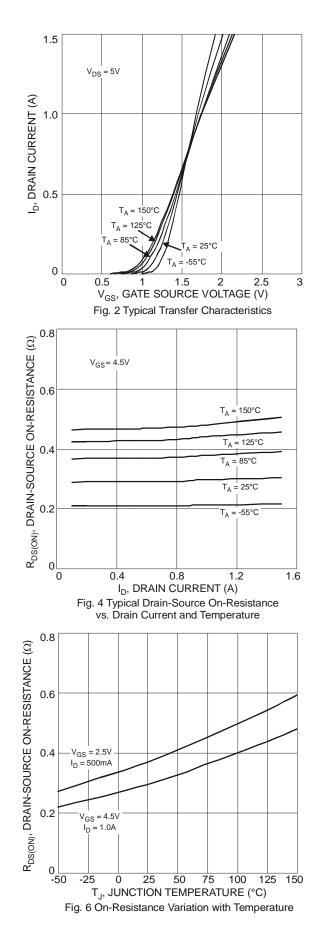
5. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

DMN2400UFB

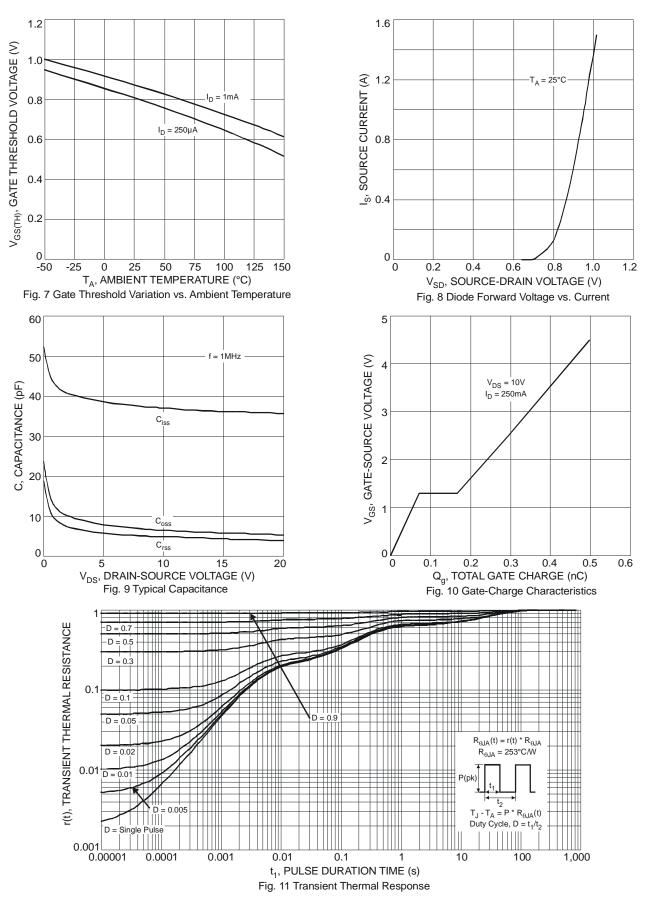






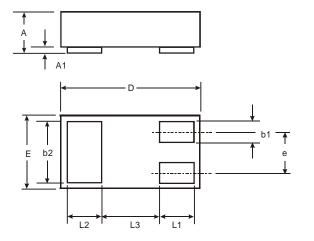
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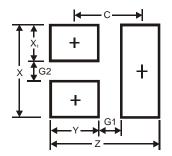


Package Outline Dimensions



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	_	_	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	_	_	0.40		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
С	0.7



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